

KSD985/986

Low Frequency Power Amplifier

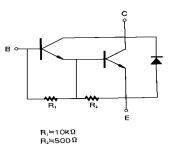
• Low Speed Switching Industrial Use



NPN Epitaxial Silicon Darlington Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	150	V
V _{CEO}	Collector-Emitter Volage		
	: KSD985	60	V
	: KSD986	80	V
V _{EBO}	Emitter-Base Voltage	8.0	V
I _C	Collector Current (DC)	1.5	Α
I _{CP}	*Collector Current (Pulse)	3.0	Α
I _B	Base Current	0.15	Α
P _C	Collector Dissipation (T _a =25°C)	1.0	W
P _C	Collector Dissipation (T _C =25°C)	10	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C



Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
I _{CBO}	Collector Cut-off Current	$V_{CB} = 60V, I_{E} = 0$			10	μΑ
I _{CER}	Collector Cut-off Current	$V_{CE} = 60V, R_{BE} = 51\Omega$ @ $T_{C} = 125^{\circ}C$			1.0	mA
I _{CEX1}	Collector Cut-off Current	$V_{CE} = 60V, V_{BE}(off) = -1.5A$ $V_{CE} = 60V, V_{BE}(off) = -1.5A$ @ $T_{C} = 125^{\circ}C$			10 1.0	μA mA
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			1.0	mA
h _{FE1} h _{FE2}	*DC Current Gain	$V_{CE} = 2V, I_{C} = 0.5A$ $V_{CE} = 2V, I_{C} = 1A$	1000 2000		30000	
V _{CE} (sat)	*Collector-Emitter Saturation Voltage	$I_C = 1A$, $I_B = 1mA$			1.5	V
V _{BE} (sat)	*Base-Emitter Saturation Voltage	$I_C = 1A$, $I_B = 1mA$			2.0	V
t _{ON}	Turn ON Time	$V_{CC} = 50V, I_{C} = 1A$		0.5		μs
t _{STG}	Storage Time	$I_{B1} = -I_{B2} = 1mA$		1.0		μs
t _F	Fall Time	$R_L = 50\Omega$		1.0		μs

^{*} Pulse Test: PW≤350μs, Duty Cycle≤2%

h_{FE} Classification

Classification	R	0	Y
h _{FE2}	2000 ~ 5000	4000 ~ 10000	8000 ~ 30000

^{*} PW≤300μs, Duty Cycle10%

Typical Characteristics

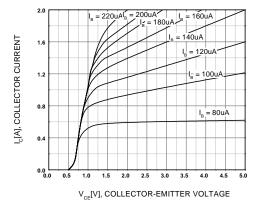


Figure 1. Static Characteristic

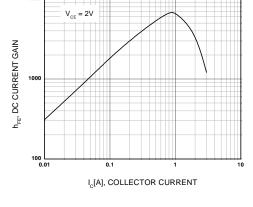


Figure 2. DC current Gain

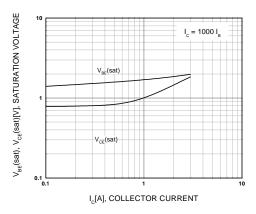


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

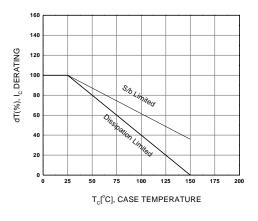


Figure 4. Derating Curve Of Safe Operating Areas

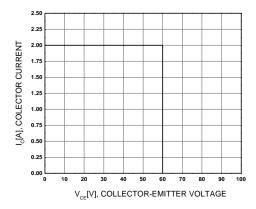


Figure 5. Reverse Bias Safe Operating Areas

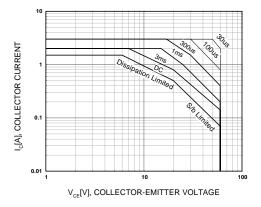


Figure 6. Safe Operating Area

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Typical Characteristics (Continued)

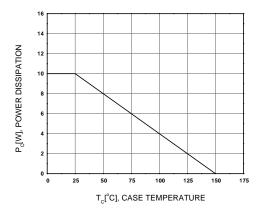


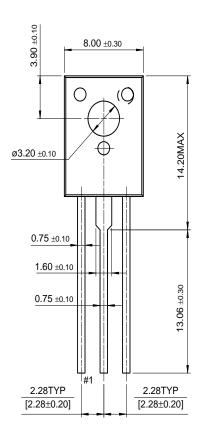
Figure 7. Power Derating

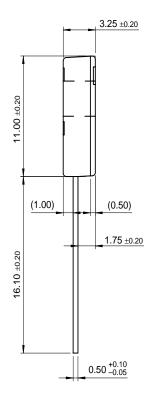
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Package Demensions

TO-126





Dimensions in Millimeters

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